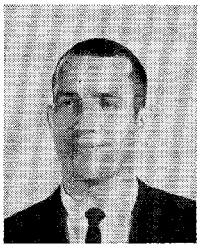
Contributors



James L. Allen (S'57–M'62) was born in Graceville, Fla., on September 25, 1936. He received the B.E.E., M.S.E.E., and Ph.D. degrees in electrical engineering from the Georgia Institute of Technology, Atlanta, in 1959, 1961, and 1966, respectively.

From January, 1959, to June, 1961, he was with the Radar Section of the Georgia Institute of Technology Engineering Experiment Station where he worked on high-speed microwave radar scanners. From June, 1961, to September, 1963, he was employed by Sperry Microwave Electronics Co., A Division of Sperry Rand Corp., Clearwater, Fla., and worked on ferrimagnetic limiters and microwave filters. He was an Instructor at the School of Electrical Engineering, Georgia Institute of Technology, from September, 1963, to March, 1966. In April, 1966, he returned to the Sperry Microwave Electronic Co. where he is currently engaged in the computer-aided design of microwave devices. He is also an Adjunct Professor in Electrical Engineering at the University of South Florida, Tampa.

Dr. Allen is a member of Sigma Xi.

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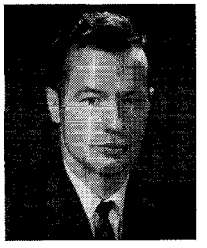
John W. Amoss (M'62) was born in Fairburn, Ga., on September 25, 1933. He received the B.E.E. degree from Auburn University, Auburn, Ala., in 1958, the M.S.E.E. degree from the Georgia Institute of Technology, Atlanta, in 1958, and has done further graduate work at Auburn University and University of South Florida.

In 1959 he joined Sperry Microwave Electronics Div., A Division of Sperry Rand Corp., Clearwater, Fla., where he is now a Senior Member of the Research Staff. His work has been in the area of parametric devices, tunnel-diode amplifiers, low-noise figure measurement techniques, system noise analysis, measurements of microwave properties of ferroelectric materials in microwave devices, and direct microwave power generation.

Mr. Amoss is a member of Eta Kappa Nu and Pi Mu Epsilon.



Norman J. Brown (S'52–A'53–M'59) was born in Ipswich, Mass., on January 26, 1928. He received the B.S. and M.S. degrees in electrical engineering from Northeastern University, Boston, Mass., in 1953 and 1957, respectively.

From 1951 to 1957 he was with Bomac Laboratories, Inc., Beverly, Mass., where he worked on gas switching (T–R) tubes. Since 1957 he has been affiliated with Microwave Associates, Inc., Burlington, Mass., where he continued his work on gas switching tubes, specializing in high-power duplexing. In 1963 he became Product Manager of the Solid-State Control Device Group.

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Martin Caulton (M'61–SM'65) was born in the Bronx, N. Y., on August 28, 1925. He received the B.S., M.S., and Ph.D. degrees in physics from the Rensselaer Polytechnic Institute, Troy, N. Y., in 1950, 1952, and 1954, respectively.

From 1950 to 1953 he was an Instructor in physics at Rensselaer Polytechnic Institute. From 1953 to 1954 he was Research Associate and simultaneously did part of his doctoral work in high-energy nuclear physics, at the Brookhaven National Laboratories, Upton, N. Y. From 1954 to 1955 he was a Fulbright scholar at the Imperial College of Science and Technology in London. From 1955 to 1958 he was a Member of the Technical Staff at Bell Telephone Laboratories, Inc., working in research and development on low-noise microwave tubes. In 1958 he became Assistant Professor of Physics at Union College, Schenectady, N. Y. Since joining RCA Laboratories, David Sarnoff Research Center, Princeton, N. J., in 1960 he has been engaged in work on microwave power tubes, multivelocity flow problems in electron beams, and microwave solid-state devices. He is a co-author of a textbook on physical electronics and is also Adjunct Professor of Electrical Engineering at Drexel Institute of Technology, Philadelphia, Pa.

Dr. Caulton is a member of the American Physical Society, American Association of Physics Teachers, and Sigma Xi.

Louis Courtois was born in Nantes, Loire-Atlantique, France, on September 6, 1936. He was graduated from the Ecole Supérieure d'Electricité, Paris, France, in 1960, and received the D.Ing. degree from the Université de Paris, in 1964.

In 1960 he joined the Microwave Group of the Laboratoire de Magnétisme et de Physique du Solide, Centre National de la Recherche Scientifique (C.N.R.S.), Bellevue, France. He was concerned with research on wave propagation in ferrites and ferrimagnetic parametric amplification. He is presently Chargé de Recherche at C.N.R.S.

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Daniel A. Daly was born in Doylestown, Ohio, on March 11, 1937. He received the B.S. degree in electrical engineering from Case Institute of Technology, Cleveland, Ohio, in 1959 and the M.S. degree in electrical engineering from Rutgers University, New Brunswick, N. J., in 1961.

Since 1959 he has worked for RCA. During the first year he was in Microwave Products at Harrison, N. J. In 1960 he became a member of the Technical Staff of the RCA Laboratories, David Sarnoff Research Center, Princeton, N. J., where he has worked on multivelocity flow problems in electron beams, microwave window problems, and integrated microwave techniques.

Mr. Daly is a member of Sigma Xi.

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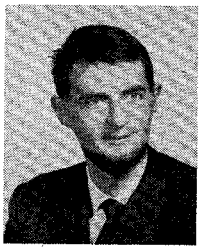

Jean Louis Dormann was born in Badonviller, Meurthe et Moselle, France, on September 5, 1933. He was graduated from the Ecole Nationale Supérieure d'Electricité et de Mécanique de Nancy, France, in 1956, and received the D.Ing. degree from the Université de Paris, France, in 1960.

In 1958 he joined the Microwave Group of the Laboratorie de Magnétisme et de Physique du Solide, Centre National de la Recherche Scientifique (C.N.R.S.), Bellevue, France. His concern was with theoretical research on wave propagation in ferrites. He is presently Chargé de Recherche at C.N.R.S.

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Roald Ekholdt (M'63) was born in Bergen, Norway, on February 9, 1936. He received a degree in electrical engineering from the Norwegian Institute of Technology, Trondheim, Norway, in 1961.

Upon graduation he joined the Norwegian Defense Research Establishment (NDRE), Kjeller, Norway, where he has been engaged in the design of solid-state microwave sources and amplifiers. In 1966 and 1967, on leave of absence from NDRE, he was on the staff of the Microwave Research Laboratory, RCA Laboratories, David Sarnoff Research Center, Princeton, N. J.

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Monique Gastine was born in France on December 17, 1941. She received the Lic. ès Sci. degree from the Université de Paris, France, in 1962, and is presently working towards the doctoral degree in the Microwave Group of the Laboratorie de Magnétisme et de Physique du Solide, Centre National de la Recherche Scientifique (C.N.R.S.), Bellevue, France.

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Harry Goldie (S'59–M'64) was born in Brooklyn, N. Y., on May 3, 1927. He received the B.E.E. degree from the City College of New York, N. Y., in 1960, and the M.S. degree in electrical engineering from the Polytechnic Institute of Brooklyn, N. Y., in 1963.

From 1953 to 1960 he was associated with the Department of Electrical Engineering at Cooper Union for the Advancement of Science and Art, New York, N. Y. In 1960 he joined the Research Staff of the Microwave Research Institute (now the Electrophysics Department) of the Polytechnic Institute of Brooklyn as a Research Assistant engaged in research on microwave gas discharges and development of high-power microwave components. Since 1963, he has been with the Microwave Technology Laboratory, Westinghouse Defense and Space Center, Baltimore, Md., as a Senior Engineer engaged in the development of gaseous microwave components such as TR tubes and broadband plasma switches. He is presently Group Leader of Plasma Devices and is a registered professional engineer in Maryland.

Mr. Goldie is a member of Sigma Xi.

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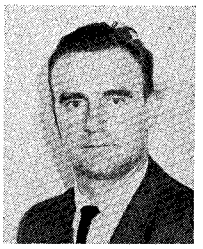

Kurt E. Gsteiger (M'58) was born in Twann, Switzerland, on April 6, 1927. He received the M.S. degree in physics from the Swiss Federal Institute of Technology, Zurich, in 1954.

From 1954 to 1956 he was associated with Philips Company in Nijmegen, Holland, and Zurich, Switzerland, working on the development of low-power germanium transistors. In 1956 he joined Ebauches S.A. in Neuchatel, Switzerland, as Technical Head of the Semiconductor Department. His responsibilities covered materials research, development and manufacture of miniature transistors for watches. In 1960 he was with the Transitron Electronic Corp., Wakefield, Mass., as Research Staff Engineer and Group Leader. He was responsible for the development of diffused silicon transistors and solar cells and the growth of epitaxial layers. From 1961 to 1964 he was associated with the Bomac Division of Varian Associates, Beverly, Mass., first as a Member of the Research Staff and later as Manager of Semiconductor Engineering. During this time he performed and directed work on varactors, switching diodes and materials preparation, and characterization. Since 1964 he has been Research Staff Consultant with the Sperry Microwave Electronics Div., Clearwater, Fla., where he has been involved in research in the field of varactors, *PIN* diodes, step-recovery diodes, gallium arsenide mixer diodes, microwave integrated circuits, and semiconductor devices for the direct generation of microwave power.

Mr. Gsteiger is a member of the American Physical Society.

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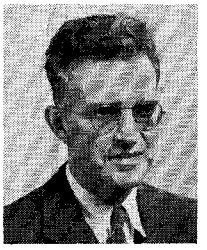

W. D. Hershberger (A'37–SM'45–F'54) was born in Wellman, Iowa, on May 10, 1903. He received the A.B. degree in mathematics from Goshen College, Goshen, Ind., in 1927, the A.M. degree in physics from George Washington University, Washington, D.C., in 1930, and the Ph.D. degree in electrical engineering from the University of Pennsylvania, Philadelphia, in 1937.

From 1927 to 1931 he was employed in the Sound Division at the Naval Research Laboratory, Washington, D. C., working in ultrasonics for submarine detection. From 1931 to 1936 he was with the Signal Corps Laboratories, Ft. Monmouth, N. J., where he was concerned with short wave and microwave work for radio detection, and from 1937 to 1949 he was with the Research Laboratories of RCA. From 1937 to 1942, he was employed at RCA, Camden, N. J., and from 1942 to 1949 at RCA Laboratories in Princeton, N. J. He was active in the development of the altimeter and obstacle detection equipment operative in flight in 1937. During this period he contributed to the fields of radar, microwave spectroscopy, frequency stabilization with ammonia absorption lines, and paramagnetic resonance. Since 1949 he has served as Professor of Engineering at the University of California, Los Angeles, working in electromagnetic theory, paramagnetic resonance, and plasma research. He served on the Board of Directors of WESCON for four years, and as Chairman in 1954. From 1955 to 1956 he was at the University of Leiden, Netherlands, as a Fulbright Research Scholar. He is presently Visiting Professor at Technische Hochschule Munchen, Germany. Fifty patents have been issued to him and he has written numerous articles.

Dr. Hershberger is a member of the American Physical Society, the American Association for the Advancement of Science, Sigma Xi, and Tau Beta Pi.

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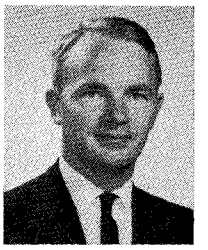

Harry Hewitt (S'60–M'62) was born in Lawrenceburg, Tenn., on September 3, 1934. He received the B.S.E.E. degree from Stanford University, Stanford, Calif., in 1960.

Since graduation he has worked at the Applied Electronics Labs., Stanford, Calif., where he has done research in designing reconnaissance receiver and radar systems utilizing pulse compression techniques. He is currently a Research Associate there.

Mr. Hewitt is a member of Sigma Xi and Tau Beta Pi.

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Stanley P. Knight (M'67) was born in Bradford, Pa., on May 26, 1939. He received the B.S.E.E. from the University of Kentucky, Lexington, in 1961, and is pursuing the M.S.E.E. degree at Newark College of Engineering, N. J.

Since 1961 he has been employed by RCA Astro-Electronics Division, Hightstown, N. J., where he designed various spacecraft communication subsystems ranging from telemetry equipment to command receivers and transmitters. He is currently in the

Astro-Electronics Division Microwave Group and is a member of the RCA Corporate-wide Blue Chip Team.

Mr. Knight is a member of Eta Kappa Nu and Tau Beta Pi.

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Yoshihiro Konishi (A'61–SM'65) was born on September 24, 1928 in Nara, Japan. He received the B.S. and Ph.D. degrees from Kyoto University, Kyoto, Japan, in 1951 and 1961, respectively.

He joined Nippon Hoso Kyokai (Japan Broadcasting Corporation), Tokyo, in 1951. Since 1952, he has worked at their Technical Research Laboratories, where he has been engaged in research and development of VHF and UHF circuits and components. From 1962 to 1963, he was at the Microwave Research Institute of the Polytechnic Institute of Brooklyn, Brooklyn, N. Y. At present he is a Senior Staff Member at the NHK Techical Research Laboratories, working on ferrimagnetic and solid-state circuits.

Dr. Konishi is a member of the Institute of Electrical Communication Engineering of Japan.

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Hiromu J. Kuno (S'61–M'63) was born in Osaka, Japan, on March 27, 1938. He received the B.S., M.S., and Ph.D. degrees in engineering from the University of California, Los Angeles in 1961, 1963, and 1966, respectively.

From June, 1961, to September, 1965, on a full-time basis and from September, 1965, to September, 1966, on a part-time basis, he was with the Electronics Division of the National Cash Register Company, Hawthorne, Calif., as an Associate Research and Senior Research Engineer. His work concerned various projects including the development of various digital and analog solid-state circuits, the characterization and application of semiconductor devices and integrated circuits, and the development of high-speed thin magnetic film memories. From September, 1965, to September, 1966, he was a Post-Graduate Research Engineer, supported by a NASA Research Grant at the University of California, Los Angeles working on the investigation of the microwave propagation in solid-state plasmas. In October, 1966, he joined the RCA Microwave Applied Research Laboratory, David Sarnoff Research Center, Princeton, N. J., as a Member of the Technical Staff where he is presently working on solid-state microwave devices and high-power semiconductor devices.

Dr. Kuno is a member of the American Physical Society and Tau Beta Pi.

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Louis J. Lavedan (M'58) was born in New Orleans, La., on November 20, 1933. He received the B.S. degree in physics from Loyola University, New Orleans, La., in 1954, and the M.S. degree in physics from Louisiana State University, Baton Rouge, in 1956.

From 1956 to 1962, he was employed by the Radio Corporation of America, Moorestown, N. J., where he was involved in various assignments concerning the design and development of microwave components, specializing in super-power duplexer design and high-power evaluation. In 1962, he joined Sperry Microwave Electronics Co., A Division of Sperry Rand Corp., Clearwater, Fla., where he has been engaged in design of microwave subsystems development, ferroelectric devices and latching-type ferrite devices.

Mr. Lavedan is a member of Sigma Pi Sigma.

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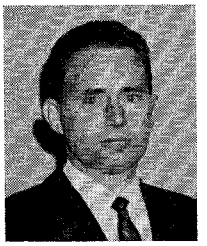
George P. Rodrigue (S'56–M'65) was born in Paincourtville, La., on June 19, 1931. He received the B.S. and M.S. degrees in physics from Louisiana State University, Baton Rouge, in 1952 and 1954, respectively, and received the Ph.D. degree in applied physics from Harvard University, Cambridge, Mass., in 1958.

During the summer of 1954 he worked with the Power Transistor Development Group at Bell Telephone Laboratories, Inc., Murray Hill, N. J. From 1954 to the present he has been with the Sperry Microwave Electronics Co., A Division of Sperry Rand Corp., Clearwater, Fla., where he has worked on microwave acoustics, parametric amplification, and microwave properties and applications of a wide variety of magnetic materials.

Dr. Rodrigue is a member of the Harvard Engineering Society, Sigma Pi Sigma, Sigma Xi, and the American Physical Society.



Donald R. Taft was born in Mendon, Mass., on October 1, 1928. He received the B.A. degree in physics from the University of New Hampshire, Durham, in 1957, and has done graduate work at the Polytechnic Institute of Brooklyn, Brooklyn, N. Y., and the University of Florida, Gainesville.

In 1957 he joined the Sperry Microwave Electronics Co., A Division of Sperry Rand Corp., Clearwater, Fla., where he has worked on the design and development of microwave ferrite devices. He is presently a Senior Member of the Research Staff of the Company.

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Dan Varon (S'62–M'66) was born in Tel-Aviv, Israel, on July 24, 1935. He received the B.S. and Dipl.Ing. degrees in electrical engineering from the Technion, Israel Institute of Technology, Haifa, Israel, in 1957 and 1961, respectively. He received the M.S. degree in electrophysics from the Polytechnic Institute of Brooklyn, N. Y., in 1963, and the Eng.Sc.D. degree from New York University, N. Y., in 1965.

In the summer of 1957 he was an exchange student working at the Telecommunication Laboratory of Van Der Heem, N.V., The Hague, Netherlands, where he participated in the design of marine communication equipment. He returned to Israel in the Fall of 1957 and served as electronics engineer in the Air Force. From 1961 to 1963 he was a Research Fellow at the Microwave Research Institute, N. Y., where he worked in lumped network synthesis. Between 1963 and 1965 he was a Teaching Fellow at New York University. Since 1965 he has been a Member of the Technical Staff at Bell Telephone Laboratories, Inc., Whippany, N. J., where he has been engaged in exploratory work on microwave transmission and phased array antennas.

Dr. Varon is a member of Eta Kappa Nu and Sigma Xi.

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Robert J. Wenzel (S'61–M'62) for a biography and photograph please see page 329 of the May 1967 issue of this TRANSACTIONS.

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